

CLF1G0035S-50

Broadband RF power GaN HEMT

Rev. 4 — 6 November 2014

Objective data sheet

1. Product profile

1.1 General description

CLF1G0035S-50 is a broadband general purpose 50 W amplifier with first generation GaN HEMT technology from NXP. Frequency of operation is from DC to 3.5 GHz.

Table 1. CW and pulsed RF application information

Typical RF performance at $T_{case} = 25\text{ }^{\circ}\text{C}$; $I_{DQ} = 150\text{ mA}$; $V_{DS} = 50\text{ V}$ in a class-AB broadband demo board.

Test signal	f	P _L	G _p	η _D
	(MHz)	(W)	(dB)	(%)
1-Tone CW	500	50	12	64
	1000	50	13	43
	1500	50	13	43
	2000	50	14	43
	2500	50	11	48
1-Tone pulsed [1]	500	50	12	65
	1000	50	15	43
	1500	50	15	43
	2000	50	15	44
	2500	50	13	49

[1] Pulsed RF; $t_p = 100\text{ }\mu\text{s}$; $\delta = 10\text{ }\%$.

Table 2. 2-Tone CW application information

Typical 2-Tone performance at $T_{case} = 25\text{ }^{\circ}\text{C}$; $I_{DQ} = 275\text{ mA}$; $V_{DS} = 50\text{ V}$ in a class-AB broadband demo board.

Test signal	f	P _{L(PEP)}	IMD3
	(MHz)	(W)	(dBc)
2-Tone CW [1]	500	10	-48
	1000	10	-40
	1500	10	-43
	2000	10	-38
	2500	10	-38

[1] 2-Tone CW; $\Delta f = 1\text{ MHz}$.



1.2 Features and benefits

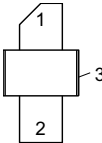
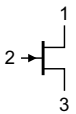
- Frequency of operation is from DC to 3.5 GHz
- 50 W general purpose broadband RF Power GaN HEMT
- Excellent ruggedness (VSWR 10 : 1)
- High voltage operation (50 V)
- Thermally enhanced package

1.3 Applications

- Commercial wireless infrastructure (cellular, WiMAX)
- Industrial, scientific, medical
- Radar
- Jammers
- Broadband general purpose amplifier
- EMC testing
- Public mobile radios
- Defense application

2. Pinning information

Table 3. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	drain		 aaa-003693
2	gate		
3	source [1]		

[1] Connected to flange.

3. Ordering information

Table 4. Ordering information

Type number	Package		
	Name	Description	Version
CLF1G0035S-50	-	earless ceramic package; 2 leads	SOT467B

4. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	150	V
V_{GS}	gate-source voltage		-8	+3	V
I_{GF}	forward gate current	external $R_G = 5 \Omega$	-	18	mA
T_{stg}	storage temperature		-65	+150	°C
T_j	junction temperature	measured via IR scan [1]	-	250	°C

[1] Continuous use at maximum temperature will affect the reliability, for details refer to the on-line MTF calculator.

5. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Typ	Unit
$R_{th(j-c)}$	thermal resistance from junction to case	$T_j = 200 \text{ °C}$	[1] 2.1	K/W

[1] T_j is measured via IR scan with case temperature of 85 °C and power dissipation of 55 W.

6. Characteristics

Table 7. DC Characteristics

$T_{case} = 25 \text{ °C}$; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{(BR)DSS}$	drain-source breakdown voltage	$V_{GS} = -7 \text{ V}$; $I_{DS} = 12 \text{ mA}$	150	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$V_{DS} = 0.1 \text{ V}$; $I_{DS} = 12 \text{ mA}$	-2.4	-2	-1.3	V
I_{DSX}	drain cut-off current	$V_{DS} = 10 \text{ V}$; $V_{GS} = 3 \text{ V}$	-	8.8	-	A
g_{fs}	forward transconductance	$V_{DS} = 10 \text{ V}$; $V_{GS} = 0 \text{ V}$	-	2.0	-	S

Table 8. RF Characteristics

Test signal: 1-Tone CW; RF performance at $V_{DS} = 50 \text{ V}$; $I_{Dq} = 150 \text{ mA}$; $f = 3 \text{ GHz}$; $T_{case} = 25 \text{ °C}$; unless otherwise specified in a class-AB production circuit.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
η_D	drain efficiency	$P_L = 50 \text{ W}$	47	54	-	%
G_p	power gain	$P_L = 50 \text{ W}$	9.8	11.5	-	dB
RL_{in}	input return loss	$P_L = 50 \text{ W}$	-	-5	-	dB

7. Application information

7.1 Demo circuit

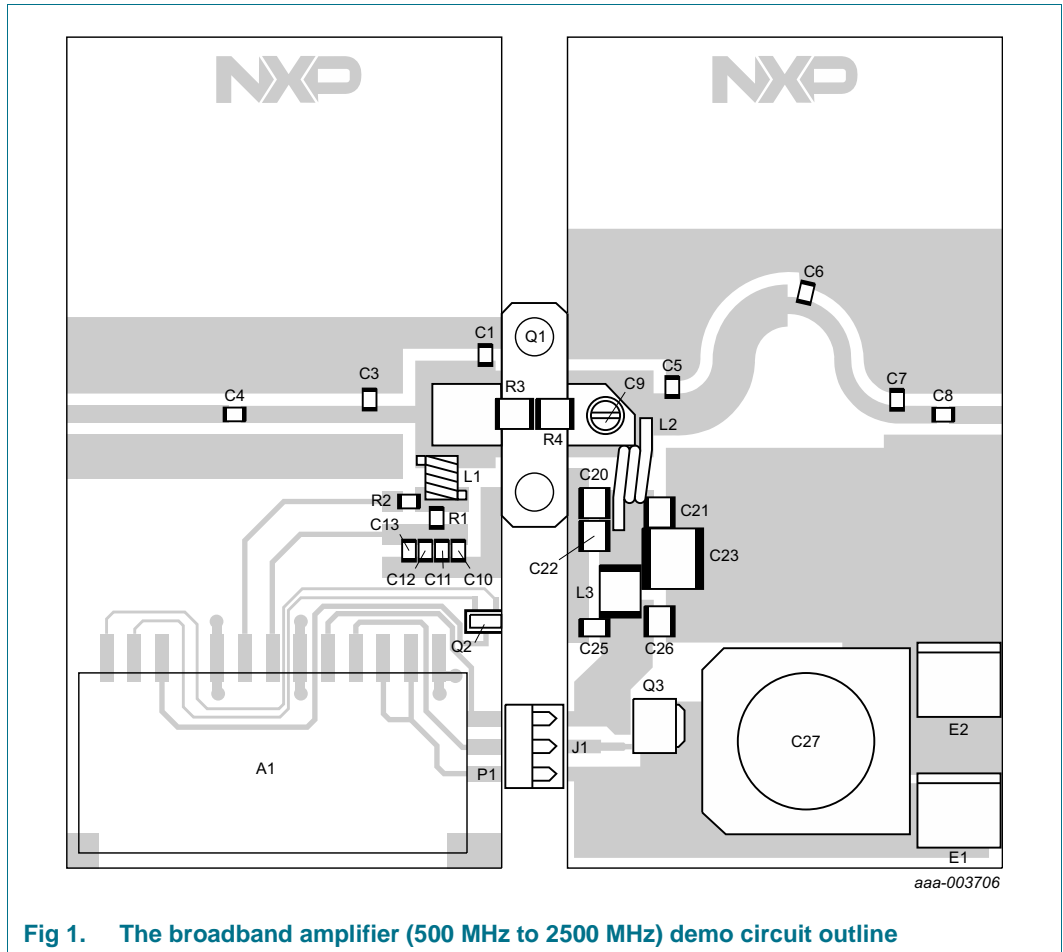


Fig 1. The broadband amplifier (500 MHz to 2500 MHz) demo circuit outline

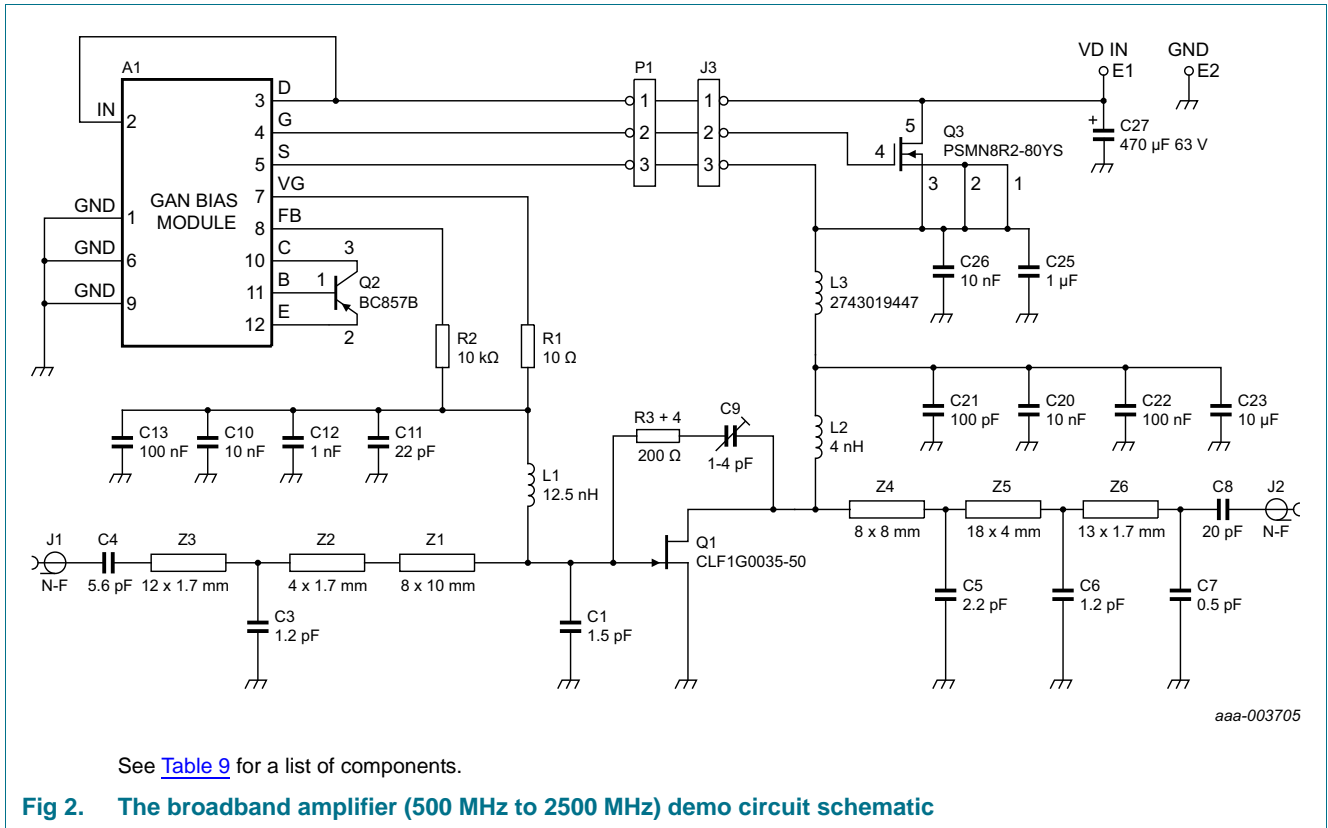
Table 9. List of components

See [Figure 1](#) and [Figure 2](#)

Component	Description	Value	Remarks
A1	GaN bias module v1	-	NXP
C1	multilayer ceramic chip capacitor	1.5 pF	ATC 600F1R5BT
C3, C6	multilayer ceramic chip capacitor	1.2 pF	ATC 600F1R2BT
C4	multilayer ceramic chip capacitor	5.6 pF	ATC 600F5R6CT
C5	multilayer ceramic chip capacitor	2.2 pF	ATC 600F2R2BT
C7	multilayer ceramic chip capacitor	0.5 pF	ATC 600F0R5BT
C8	multilayer ceramic chip capacitor	20 pF	ATC 600F200JT
C9	capacitor	1 pF to 4 pF	Tronser 66-0304-00004-000
C10	multilayer ceramic chip capacitor	10 nF	generic
C11	multilayer ceramic chip capacitor	22 pF	generic
C12	multilayer ceramic chip capacitor	1 nF	generic

Table 9. List of components ...continued
See [Figure 1](#) and [Figure 2](#)

Component	Description	Value	Remarks
C13	multilayer ceramic chip capacitor	100 nF	generic
C20	multilayer ceramic chip capacitor	1 nF	ATC 100B102KW
C21	multilayer ceramic chip capacitor	100 pF	ATC 100B101JW
C22, C26	multilayer ceramic chip capacitor	10 nF	generic
C23	multilayer ceramic chip capacitor	10 μ F	TDK C5750X7S2A106M
C25	multilayer ceramic chip capacitor	1 μ F	generic
C27	electrolytic capacitor	470 μ F	Panasonic EEE-TK1J471AM
E1, E2	drain voltage connection	-	
J1	RF in connector	-	
J2	RF out connector	-	
J3, P1	1 row, 3-way vertical DC connector header	-	
L1	inductor	12.5 nH	Coil craft A04T
L2	inductor	4 nH	
L3	ferrite bead	-	Fair-Rite 2743019447
Q1	transistor	-	NXP CLF1G0035-50
Q2	transistor	-	NXP BC857B
Q3	transistor	-	NXP PSMN8R2-80YS
R1	resistor,	10 Ω	generic
R2	resistor	10.0 k Ω	generic
R3, R4	resistor	100 Ω	generic
Z1, Z2, Z3, Z4, Z5, Z6	microstrip lines	-	



7.2 Application test results

Table 10. CW and pulsed RF application information

Typical RF performance at $T_{case} = 25\text{ }^{\circ}\text{C}$; $I_{Dq} = 150\text{ mA}$; $V_{DS} = 50\text{ V}$ in a class-AB broadband demo board.

Test signal	f (MHz)	P_L (W)	G_p (dB)	η_D (%)
1-Tone CW	500	50	12	64
	1000	50	13	43
	1500	50	13	43
	2000	50	14	43
	2500	50	11	48
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	1000	50	15	43
	1500	50	15	43
	2000	50	15	44
	2500	50	13	49

[1] Pulsed RF; $t_p = 100\text{ }\mu\text{s}$; $\delta = 10\text{ }\%$.

Table 11. 2-Tone CW application information

Typical 2-Tone performance at $T_{case} = 25\text{ }^{\circ}\text{C}$; $I_{Dq} = 275\text{ mA}$; $V_{DS} = 50\text{ V}$ in a class-AB broadband demo board.

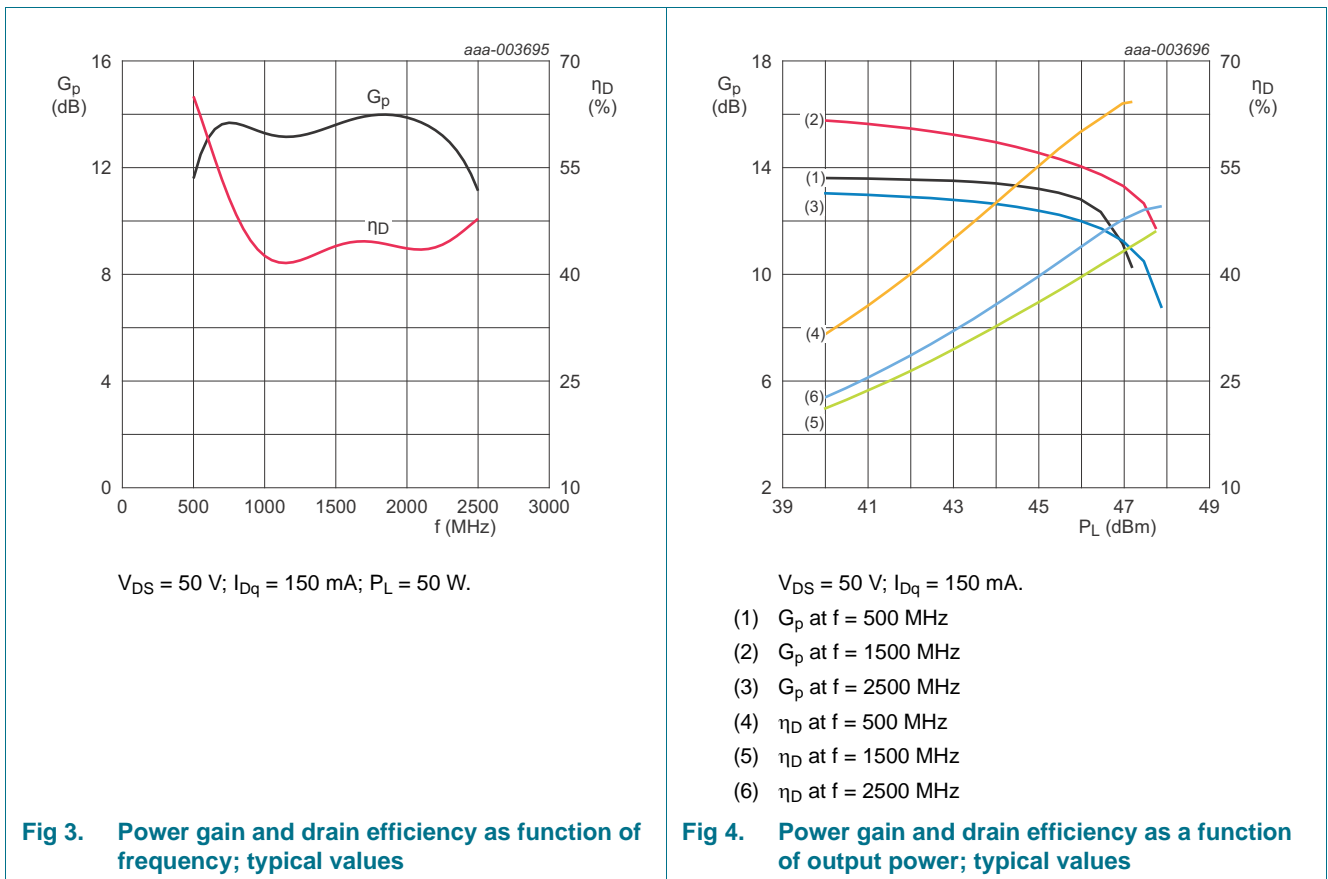
Test signal	f (MHz)	$P_{L(PEP)}$ (W)	IMD3 (dBc)
2-Tone CW [1]	500	10	-48
	1000	10	-40
	1500	10	-43
	2000	10	-38
	2500	10	-38

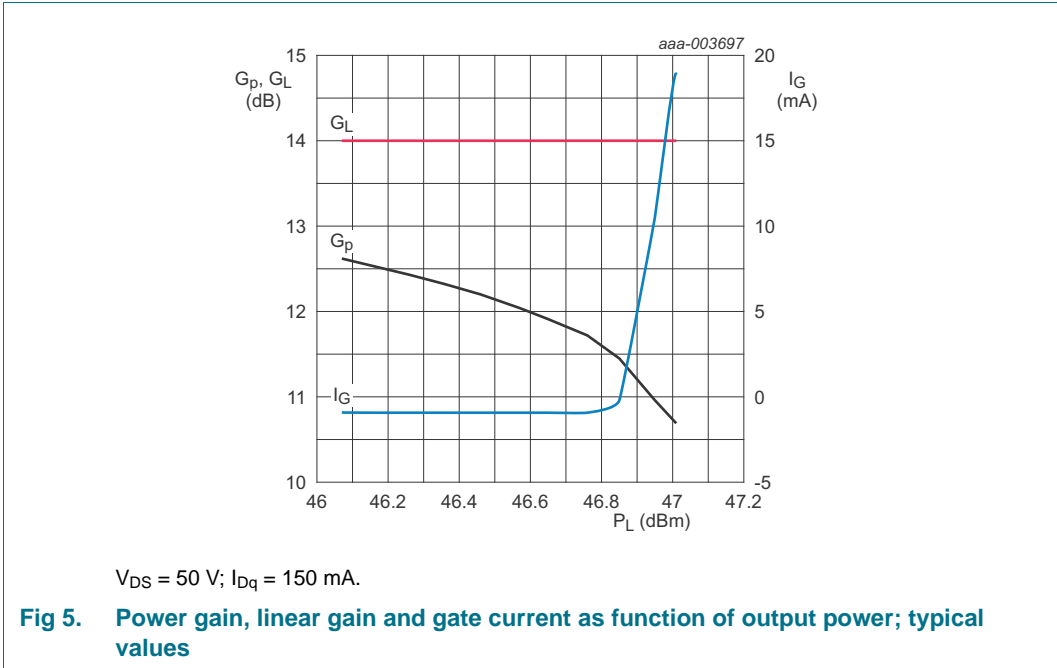
[1] 2-Tone CW; $\Delta f = 1\text{ MHz}$.

7.3 Graphical data

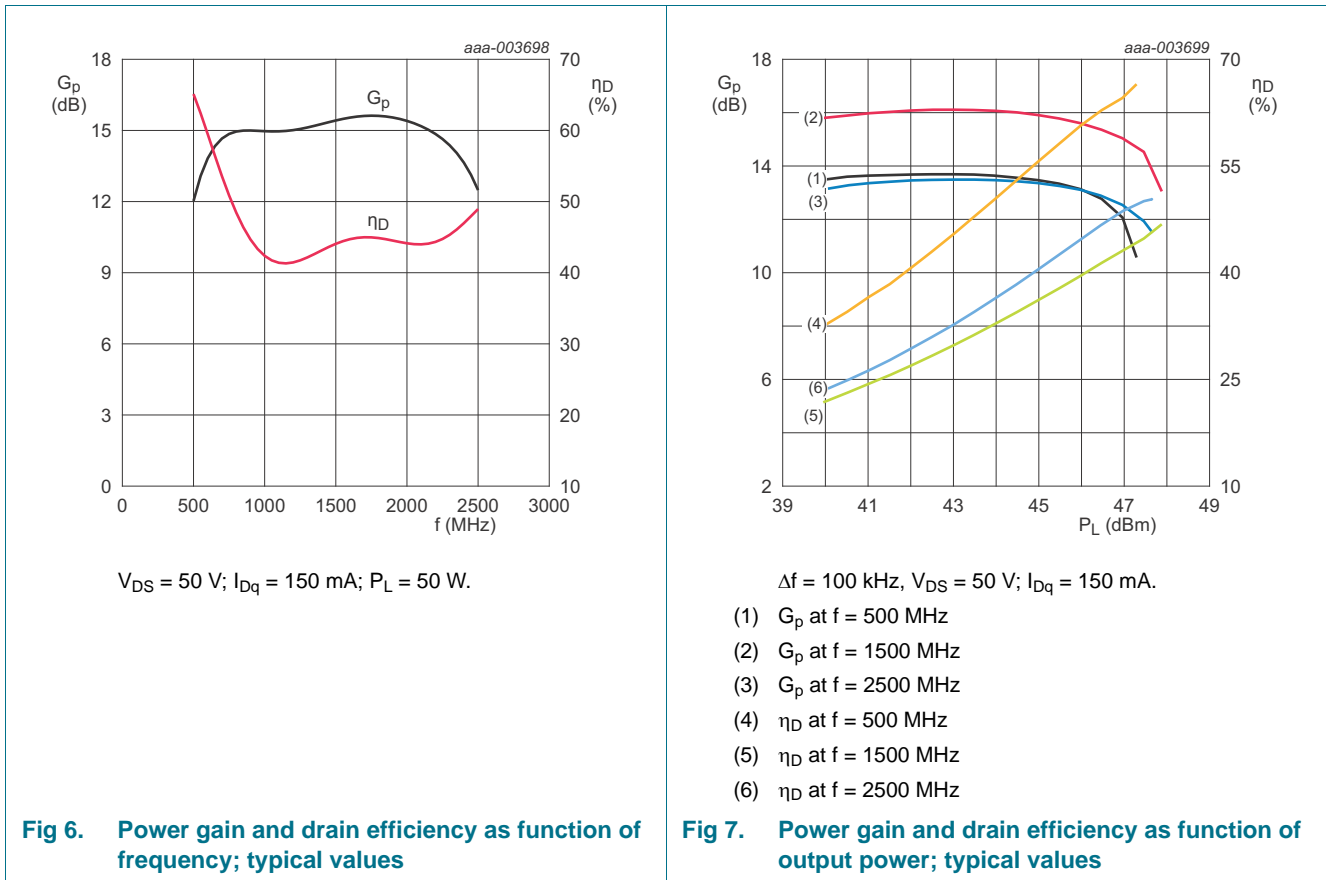
The following figures are measured in a broadband amplifier demo board from 500 MHz to 2500 MHz.

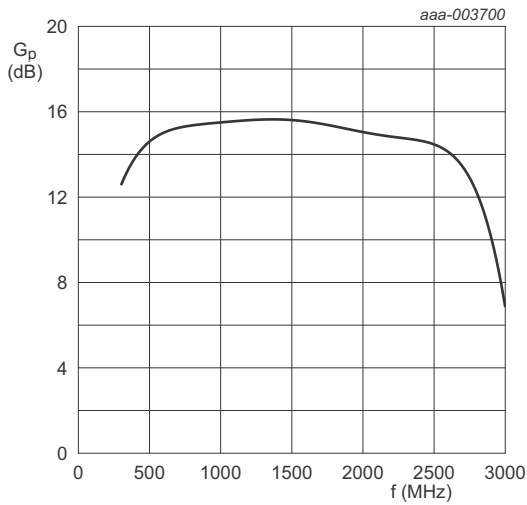
7.3.1 1-Tone CW RF performance





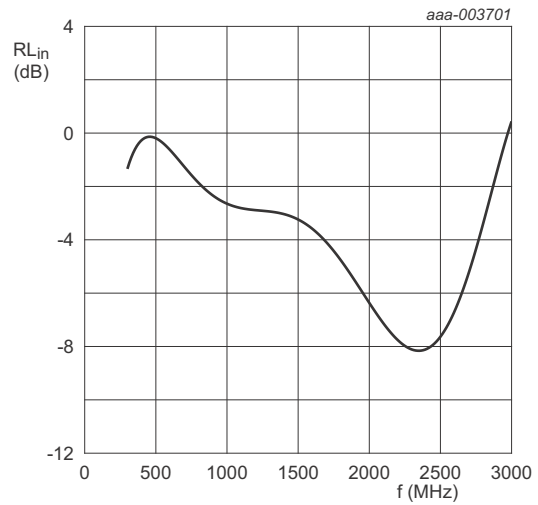
7.3.2 1-Tone pulsed RF performance





$P_i = 10 \text{ dBm}$, $V_{DS} = 50 \text{ V}$; $I_{Dq} = 150 \text{ mA}$.

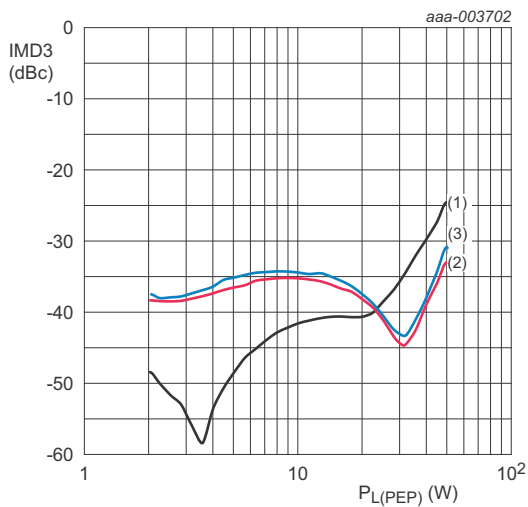
Fig 8. Power gain as a function of frequency; typical values



$P_i = 10 \text{ dBm}$, $V_{DS} = 50 \text{ V}$; $I_{Dq} = 150 \text{ mA}$.

Fig 9. Input return loss as a function of frequency; typical values

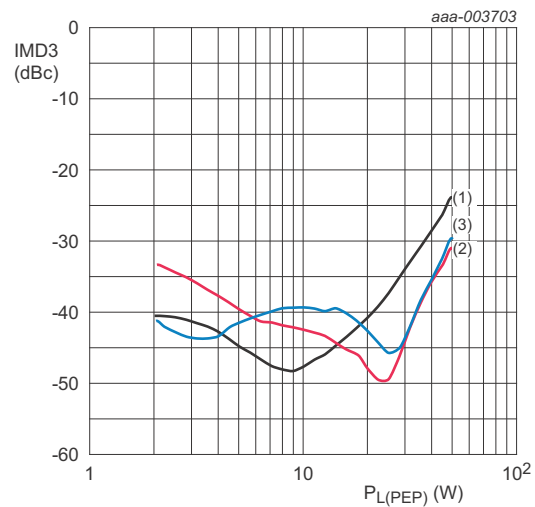
7.3.3 2-Tone CW performance



$\Delta f = 1 \text{ MHz}$; $V_{DS} = 50 \text{ V}$; $I_{Dq} = 150 \text{ mA}$.

- (1) $f = 500 \text{ MHz}$
- (2) $f = 1500 \text{ MHz}$
- (3) $f = 2500 \text{ MHz}$

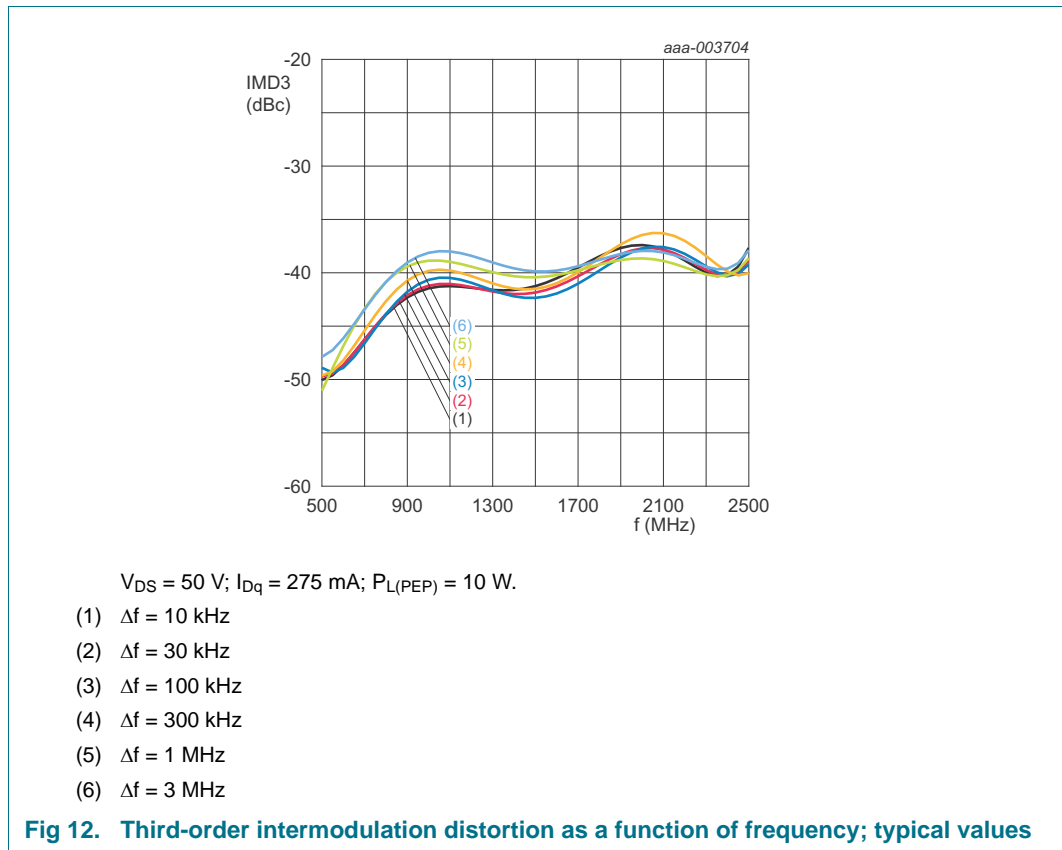
Fig 10. Third-order intermodulation distortion as a function of peak envelope power load power; typical values



$\Delta f = 1 \text{ MHz}$; $V_{DS} = 50 \text{ V}$; $I_{Dq} = 275 \text{ mA}$.

- (1) $f = 500 \text{ MHz}$
- (2) $f = 1500 \text{ MHz}$
- (3) $f = 2500 \text{ MHz}$

Fig 11. Third-order intermodulation distortion as a function of peak envelope power load power; typical values



7.4 Bias module

The bias module information for the GaN HEMT amplifier is described in application note AN11130.

8. Test information

8.1 Ruggedness in class-AB operation

The CLF1G0035S-50 is capable of withstanding a load mismatch corresponding to $V_{SWR} = 10 : 1$ through all phases under the following conditions: $V_{DS} = 50 \text{ V}; P_L = 50 \text{ W (CW)}, f = 2500 \text{ MHz}.$

8.2 Load pull impedance information

The measured load pull impedances are shown below. Impedance reference plane defined at device leads. Measurements performed with NXP test fixtures. Test temperature set at $25 \text{ }^\circ\text{C}$ with a CW signal.

Table 12. Typical impedance

Typical values unless otherwise specified.

f (MHz)	Z _S (Ω)	Z _L (maximum P _{L(M)}) (Ω)	Z _L (maximum η _D) (Ω)
500	6.4 + 4j	9.7 + 7j	10 + 5.0j
1000	1.9 + 2.2j	9.1 + 12.4j	10 + 6.0j
2000	1.9 – 2.9j	5 + 4.1j	6.6 + 1.4j
2500	2.1 – 6.3j	3.6 + 0.75j	4.5 – 0.4 j
3000	2.5 – 9j	3.9 – 1.2j	5.8 – 1.8j
3500	2.9 – 14j	6.6 – 2j	5.8 – 3j

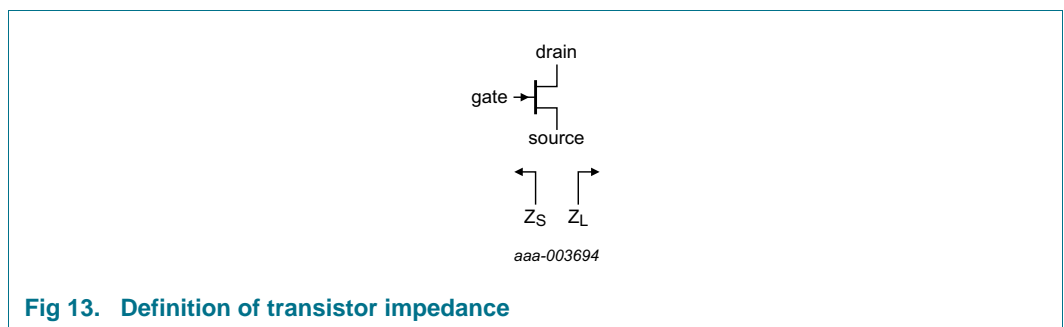


Fig 13. Definition of transistor impedance

Z_S is the measured source pull impedance presented to the device. Z_L is the measured load pull impedance presented to the device.

8.3 Packaged S-parameter data

Table 13. S-parameter

Small signal; $V_{DS} = 50\text{ V}$; $I_{Dq} = 150\text{ mA}$; $Z_S = Z_L = 50\ \Omega$

f (MHz)	S ₁₁		S ₂₁		S ₁₂		S ₂₂	
	Magnitude (ratio)	Angle (degree)	Magnitude (ratio)	Angle (degree)	Magnitude (ratio)	Angle (degree)	Magnitude (ratio)	Angle (degree)
500	0.82686	-168.9	9.6028	67.238	0.01482	-9.5809	0.48482	-133.17
600	0.82717	-171.62	7.7589	61.123	0.013844	-12.463	0.52053	-136.01
700	0.82892	-173.81	6.4386	55.547	0.01282	-14.415	0.55589	-138.65
800	0.83183	-175.69	5.4524	50.412	0.011783	-15.413	0.58964	-141.17
900	0.83572	-177.39	4.6934	45.655	0.010764	-15.358	0.62126	-143.61
1000	0.84047	-178.98	4.096	41.233	0.0097946	-14.091	0.65063	-145.96
1100	0.84604	179.5	3.618	37.11	0.008907	-11.409	0.67787	-148.22
1200	0.85244	178	3.2306	33.257	0.0081421	-7.0907	0.70319	-150.39
1300	0.8597	176.51	2.9136	29.648	0.0075495	-0.99281	0.72687	-152.47
1400	0.86785	175.01	2.6525	26.259	0.0071873	6.7932	0.74919	-154.47
1500	0.87697	173.47	2.4362	23.07	0.0071125	15.766	0.77044	-156.39
1600	0.88715	171.88	2.2569	20.062	0.0073641	25.034	0.79086	-158.24
1700	0.89848	170.23	2.1083	17.22	0.007952	33.645	0.81069	-160.04
1800	0.90446	168.57	1.972	14.461	0.0088014	40.908	0.8252	-161.7
1900	0.90172	166.97	1.839	11.713	0.0098257	46.58	0.83233	-163.2
2000	0.89927	165.33	1.7253	9.0465	0.011062	50.849	0.83898	-164.63
2100	0.89713	163.64	1.6281	6.4503	0.012486	53.942	0.84528	-166
2200	0.89532	161.88	1.5454	3.9129	0.014088	56.092	0.85135	-167.32
2300	0.89386	160.04	1.4755	1.4231	0.015869	57.498	0.85727	-168.6
2400	0.89277	158.1	1.4171	-1.0309	0.01784	58.314	0.86313	-169.84
2500	0.89205	156.03	1.3692	-3.4611	0.020023	58.659	0.86899	-171.05
2600	0.89096	153.83	1.3297	-5.8933	0.022423	58.605	0.87436	-172.23
2700	0.88445	151.58	1.2888	-8.4222	0.024891	58.132	0.87579	-173.35
2800	0.87762	149.17	1.2551	-10.982	0.027588	57.364	0.87715	-174.44
2900	0.87039	146.59	1.2281	-13.588	0.030547	56.329	0.87847	-175.5
3000	0.86268	143.8	1.2076	-16.259	0.033808	55.045	0.8798	-176.54
3100	0.85434	140.75	1.1934	-19.013	0.037423	53.519	0.88118	-177.56
3200	0.84525	137.4	1.1855	-21.877	0.041451	51.748	0.88265	-178.56
3300	0.83522	133.68	1.1839	-24.877	0.045967	49.721	0.88425	-179.53
3400	0.82403	129.52	1.1889	-28.05	0.051058	47.418	0.88607	179.52
3500	0.80856	125.24	1.1872	-31.326	0.056194	44.92	0.88556	178.56
3600	0.79077	120.6	1.1867	-34.765	0.061705	42.174	0.88468	177.6
3700	0.77106	115.45	1.1896	-38.412	0.067742	39.146	0.88406	176.66
3800	0.74926	109.7	1.1956	-42.297	0.074348	35.812	0.88382	175.74
3900	0.72527	103.23	1.2044	-46.449	0.081559	32.146	0.88412	174.82
4000	0.69912	95.917	1.2152	-50.902	0.089394	28.121	0.88516	173.9
4100	0.67108	87.595	1.2274	-55.686	0.097849	23.71	0.88717	172.98

Table 13. S-parameter ...continued

Small signal; $V_{DS} = 50$ V; $I_{Dq} = 150$ mA; $Z_S = Z_L = 50 \Omega$

f (MHz)	S ₁₁		S ₂₁		S ₁₂		S ₂₂	
	Magnitude (ratio)	Angle (degree)	Magnitude (ratio)	Angle (degree)	Magnitude (ratio)	Angle (degree)	Magnitude (ratio)	Angle (degree)
4200	0.64183	78.092	1.24	-60.826	0.10688	18.891	0.89042	172.03
4300	0.6126	67.228	1.2515	-66.34	0.11639	13.65	0.89516	171.03
4400	0.58534	54.856	1.2604	-72.231	0.12622	7.9864	0.90159	169.95
4500	0.5628	40.93	1.2649	-78.48	0.13615	1.9193	0.90984	168.75
4600	0.54816	25.608	1.2633	-85.047	0.14588	-4.5074	0.91983	167.38
4700	0.54433	9.3292	1.2542	-91.862	0.15511	-11.224	0.9313	165.79
4800	0.55279	-7.214	1.2369	-98.835	0.16356	-18.138	0.94381	163.95
4900	0.57293	-23.266	1.2115	-105.86	0.17103	-25.144	0.95677	161.82
5000	0.60219	-38.234	1.1791	-112.84	0.17745	-32.138	0.96962	159.39
5100	0.63534	-51.341	1.1406	-119.47	0.18272	-38.825	0.9807	156.67
5200	0.66527	-61.779	1.0972	-125.31	0.18683	-44.756	0.98704	153.74
5300	0.69493	-71.079	1.0544	-130.96	0.1906	-50.53	0.99214	150.52
5400	0.72195	-78.947	1.0134	-136.23	0.19423	-55.963	0.99508	147.04
5500	0.74577	-85.567	0.97537	-141.15	0.19795	-61.088	0.99579	143.28
5600	0.76759	-91.49	0.94075	-146	0.20193	-66.161	0.99532	139.15
5700	0.78744	-96.798	0.90986	-150.8	0.20632	-71.236	0.99371	134.58
5800	0.80548	-101.57	0.88283	-155.64	0.21125	-76.374	0.99093	129.47
5900	0.82197	-105.86	0.85961	-160.58	0.21682	-81.647	0.98694	123.72
6000	0.83722	-109.72	0.84	-165.71	0.22309	-87.14	0.98164	117.18

9. Package outline

Earless ceramic package; 2 leads

SOT467B

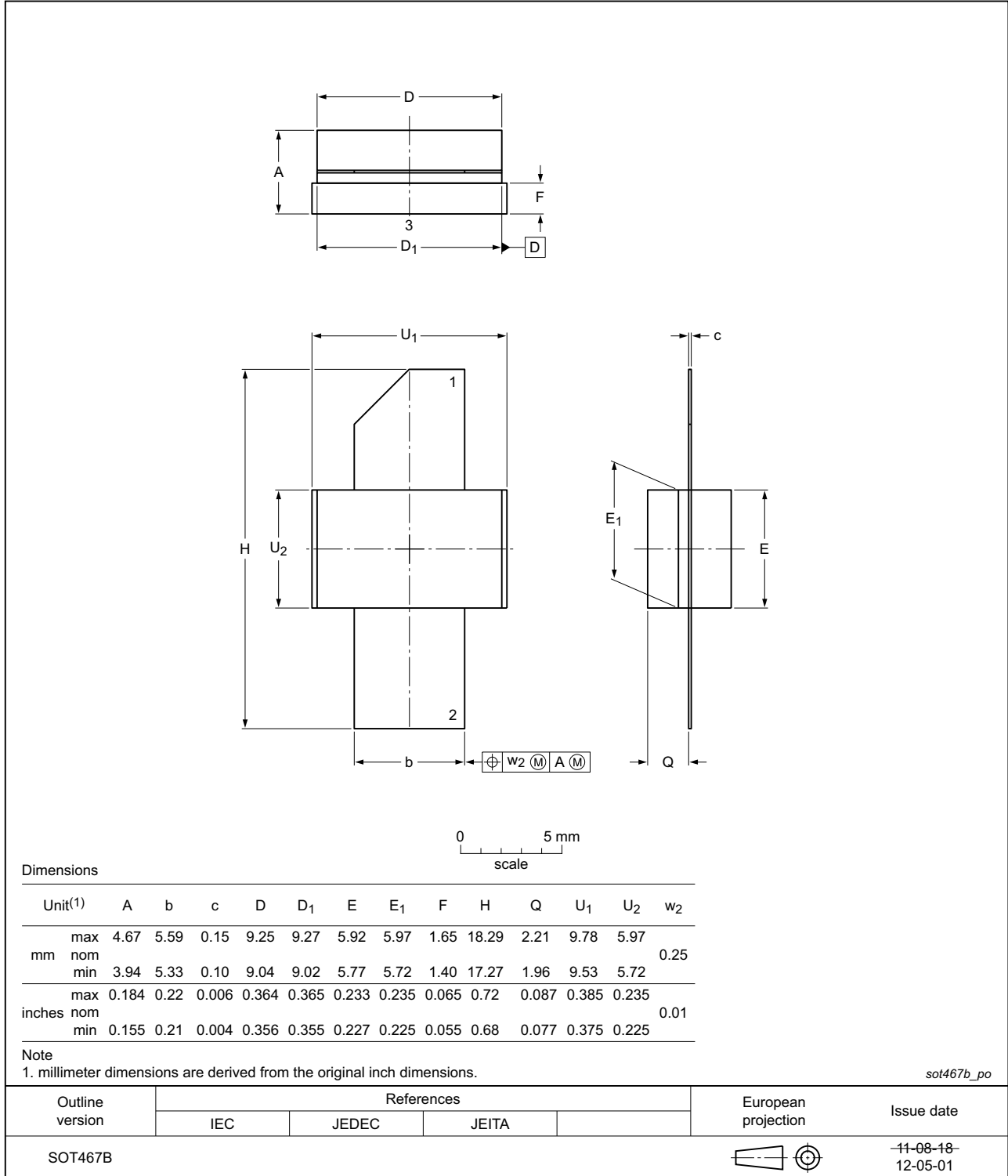


Fig 14. Package outline SOT467B

10. Handling information

10.1 ESD Sensitivity

Table 14. ESD sensitivity

ESD model	Class
Human Body Model (HBM); According JEDEC standard JESD22-A114F	1B [1]

[1] Classification 1B is granted to any part that passes after exposure to an ESD pulse of 500 V, but fails after exposure to an ESD pulse of 1000 V.

11. Abbreviations

Table 15. Abbreviations

Acronym	Description
CW	Continuous Wave
EMC	ElectroMagnetic Compatibility
ESD	ElectroStatic Discharge
GaN	Gallium Nitride
HEMT	High Electron Mobility Transistor
MTF	Median Time to Failure
VSWR	Voltage Standing-Wave Ratio
WiMAX	Worldwide Interoperability for Microwave Access

12. Revision history

Table 16. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
CLF1G0035S-50 v.4	20141106	Objective data sheet	-	CLF1G0035-50_1G0035S-50 v.3
Modifications:	<ul style="list-style-type: none"> The document now describes only the earless version of this product: CLF1G0035S-50. 			
CLF1G0035-50_1G0035S-50 v.3	20140926	Objective data sheet	-	CLF1G0035-50_1G0035S-50 v.2
CLF1G0035-50_1G0035S-50 v.2	20130129	Objective data sheet	-	CLF1G0035-50_1G0035S-50 v.1
CLF1G0035-50_1G0035S-50 v.1	20120615	Objective data sheet	-	-

13. Legal information

13.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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